



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

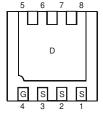
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.0172 grams (approximate)







TOP VIEW **BOTTOM VIEW**

TOP VIEW Internal Schematic

BOTTOM VIEW Pin Configuration

Maximum Ratings @ $T_A = 25$ °C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	30	V	
Gate-Source Voltage			V _{GSS}	±25	V
Drain Current (Note 3)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I _D	7.44 4.82	А
Pulsed Drain Current (Note 4)			I _{DM}	40	A

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 3)	P_{D}	0.94	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	133	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- No purposefully added lead.
 Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

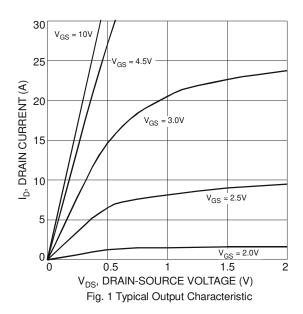


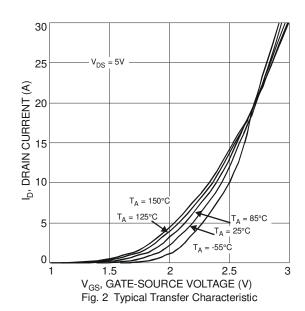
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	٧	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current TJ = 25°C	I _{DSS}	1	-	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	8.0	-	1.5	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D (-)	_	11	17	mΩ	$V_{GS} = 10V, I_D = 9A$	
Static Drain-Source On-Hesistance	R _{DS (ON)}		15	24		$V_{GS} = 4.5V, I_D = 7A$	
Forward Transfer Admittance	Y _{fs}	1	8	-	S	$V_{DS} = 10V, I_D = 9A$	
Diode Forward Voltage	V_{SD}	-	0.7	1.0	٧	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	-	798	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	128	-	pF		
Reverse Transfer Capacitance	C_{rss}	ı	122	-	рF		
Gate Resistance	R_{g}	1	1.37	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_g	ı	9.47	-	nC	$V_{GS} = 5V, V_{DS} = 15V,$ $I_{D} = 9A$	
Gate-Source Charge	Q_{gs}	-	1.87	-	nC		
Gate-Drain Charge	Q_{gd}	-	5.60	-	nC		
Turn-On Delay Time	t _{D(on)}	-	5.03	-	ns	V _{DD} = 15V, V _{GEN} = 10V,	
Turn-On Rise Time	t _r	-	4.50	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	26.33	-	ns	$R_L = 15\Omega$, $R_G = 6\Omega$, $I_D = 1A$	
Turn-Off Fall Time	t _f	-	8.55	-	ns		

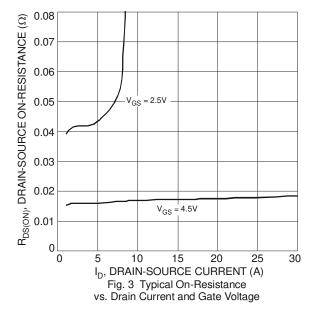
Notes:

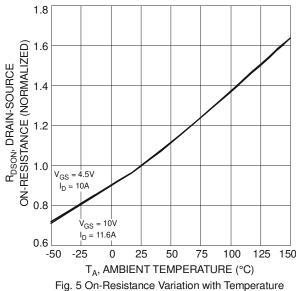
- 5. Short duration pulse test used to minimize self-heating effect.
- 6. Guaranteed by design. Not subject to product testing.

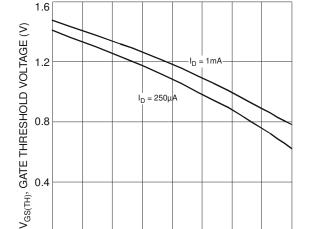












 $\label{eq:TA} {\rm T_A, AMBIENT\,TEMPERATURE}\;(^{\rm o}{\rm C})$ Fig. 7 Gate Threshold Variation vs. Ambient Temperature

50

75

100

125

25

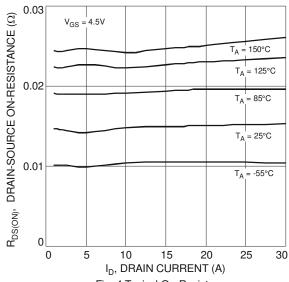


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

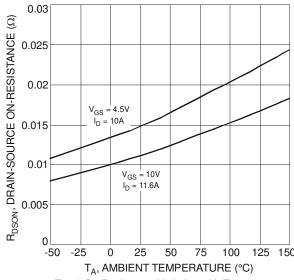
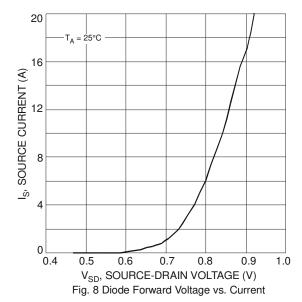
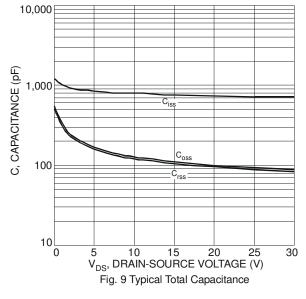


Fig. 6 On-Resistance Variation with Temperature



-25





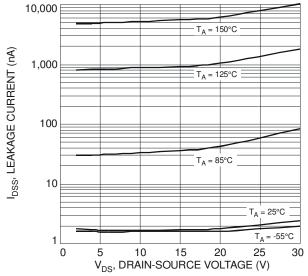
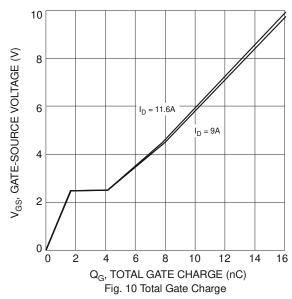


Fig. 11 Typical Leakage Current vs. Drain-Source Voltage



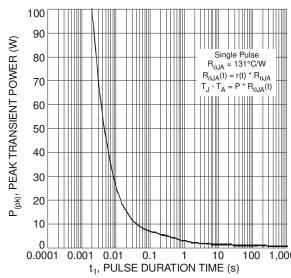


Fig. 12 Single Pulse Maximum Power Dissipation

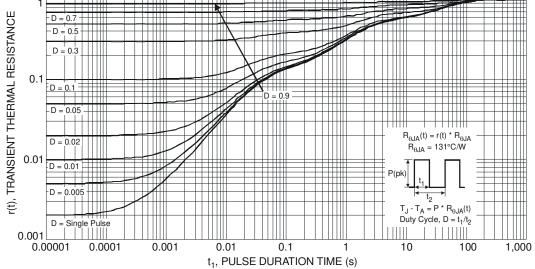


Fig. 13 Transient Thermal Response



Ordering Information (Note 7)

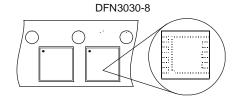
Part Number	Case	Packaging
DMG4800LFG-7	DFN3030-8	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

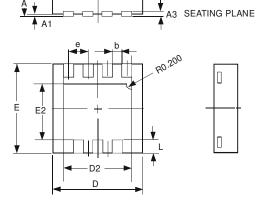
Marking Information



N48 = Product marking code YYWW = Date code marking YY = Last digit of year (ex: 09 for 2009) WW = Week code 01 to 52

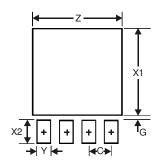


Package Outline Dimensions



DFN3030-8				
Dim	Min	Max	Тур	
Α	0.57	0.63	0.60	
A 1	0	0.05	0.02	
А3			0.15	
b	0.29	0.39	0.34	
D	2.90	3.10	3.00	
D2	2.19	2.39	2.29	
е			0.65	
Е	2.90	3.10	3.00	
E2	1.64	1.84	1.74	
L	0.30	0.60	0.45	
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.59
G	0.11
X1	2.49
X2	0.65
Υ	0.39
С	0.65



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